

**2SC3068**

High h_{FE} , Low-Frequency General-Purpose Amplifier Applications

Applications

- Low-frequency, general-purpose amplifier., various drivers, muting circuit.

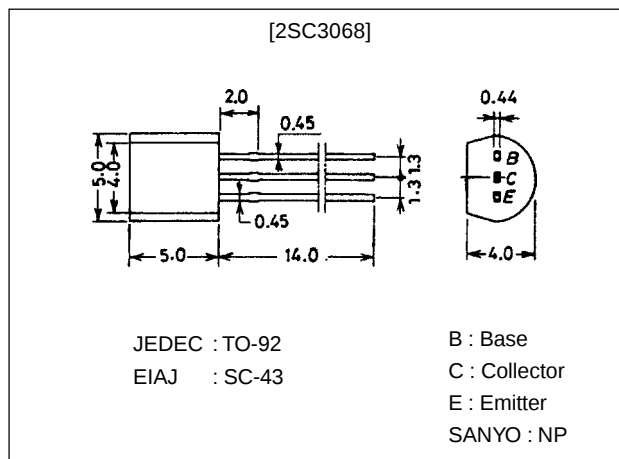
Features

- High DC current gain ($h_{FE}=800$ to 3200).
- Large current capacity.
- Low collector-to-emitter saturation voltage ($V_{CE(sat)}=0.5V$ max).
- High V_{EBO} ($V_{EBO}\geq 15V$).

Package Dimensions

unit:mm

2003A



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		30	V
Collector-to-Emitter Voltage	V_{CEO}		25	V
Emitter-to-Base Voltage	V_{EBO}		15	V
Collector Current	I_C		300	mA
Collector Current (Pulse)	I_{CP}		500	mA
Base Current	I_B		60	mA
Collector Dissipation	P_C		600	mW
Junction Temperature	T_J		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=10V, I_C=0$			0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=10mA$	800	1500	3200	
	h_{FE2}	$V_{CE}=5V, I_C=200mA$	600			
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=10mA$		250		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		4.5		pF

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=4mA$		0.12	0.5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=200mA, I_B=4mA$		0.85	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	25			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	15			V

